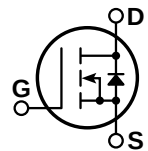
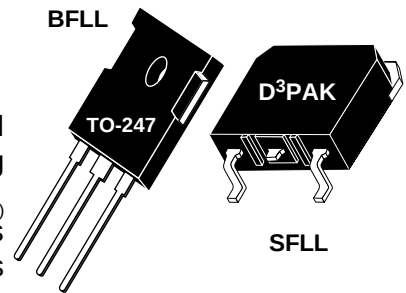


## POWER MOS 7® FREDFET

Power MOS 7® is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETs. Both conduction and switching losses are addressed with Power MOS 7® by significantly lowering  $R_{DS(on)}$  and  $Q_g$ . Power MOS 7® combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.

- Lower Input Capacitance
- Lower Miller Capacitance
- Lower Gate Charge,  $Q_g$
- Increased Power Dissipation
- Easier To Drive
- TO-247 or Surface Mount D<sup>3</sup>PAK Package
- **FAST RECOVERY BODY DIODE**



### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

| Symbol         | Parameter                                                      | APT10090   | UNIT                |
|----------------|----------------------------------------------------------------|------------|---------------------|
| $V_{DSS}$      | Drain-Source Voltage                                           | 1000       | Volts               |
| $I_D$          | Continuous Drain Current @ $T_C = 25^\circ\text{C}$            | 12         | Amps                |
| $I_{DM}$       | Pulsed Drain Current <sup>①</sup>                              | 48         |                     |
| $V_{GS}$       | Gate-Source Voltage Continuous                                 | $\pm 30$   | Volts               |
| $V_{GSM}$      | Gate-Source Voltage Transient                                  | $\pm 40$   |                     |
| $P_D$          | Total Power Dissipation @ $T_C = 25^\circ\text{C}$             | 298        | Watts               |
|                | Linear Derating Factor                                         | 2.4        | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range               | -55 to 150 | $^\circ\text{C}$    |
| $T_L$          | Lead Temperature: 0.063" from Case for 10 Sec.                 | 300        |                     |
| $I_{AR}$       | Avalanche Current <sup>①</sup> (Repetitive and Non-Repetitive) | 12         | Amps                |
| $E_{AR}$       | Repetitive Avalanche Energy <sup>①</sup>                       | 30         | mJ                  |
| $E_{AS}$       | Single Pulse Avalanche Energy <sup>④</sup>                     | 1210       |                     |

### STATIC ELECTRICAL CHARACTERISTICS

| Symbol       | Characteristic / Test Conditions                                                                   | MIN  | TYP | MAX       | UNIT    |
|--------------|----------------------------------------------------------------------------------------------------|------|-----|-----------|---------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu A$ )                                   | 1000 |     |           | Volts   |
| $I_{D(on)}$  | On State Drain Current <sup>②</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ ) | 12   |     |           | Amps    |
| $R_{DS(on)}$ | Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10V, 6A$ )                               |      |     | 0.90      | Ohms    |
| $I_{DSS}$    | Zero Gate Voltage Drain Current ( $V_{DS} = 1000V, V_{GS} = 0V$ )                                  |      |     | 250       | $\mu A$ |
|              | Zero Gate Voltage Drain Current ( $V_{DS} = 800V, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )          |      |     | 1000      |         |
| $I_{GSS}$    | Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )                                    |      |     | $\pm 100$ | nA      |
| $V_{GS(th)}$ | Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 1mA$ )                                            | 3    |     | 5         | Volts   |



**CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

# DYNAMIC CHARACTERISTICS

APT10090BFL - SFL

| Symbol       | Characteristic               | Test Conditions                                                                                                  | MIN | TYP  | MAX | UNIT    |
|--------------|------------------------------|------------------------------------------------------------------------------------------------------------------|-----|------|-----|---------|
| $C_{iss}$    | Input Capacitance            | $V_{GS} = 0V$<br>$V_{DS} = 25V$<br>$f = 1\text{ MHz}$                                                            |     | 1969 |     | pF      |
| $C_{oss}$    | Output Capacitance           |                                                                                                                  |     | 332  |     |         |
| $C_{rss}$    | Reverse Transfer Capacitance |                                                                                                                  |     | 55   |     |         |
| $Q_g$        | Total Gate Charge ③          | $V_{GS} = 10V$<br>$V_{DD} = 500V$<br>$I_D = 12A @ 25^\circ C$                                                    |     | 71   |     | nC      |
| $Q_{gs}$     | Gate-Source Charge           |                                                                                                                  |     | 12   |     |         |
| $Q_{gd}$     | Gate-Drain ("Miller") Charge |                                                                                                                  |     | 47   |     |         |
| $t_{d(on)}$  | Turn-on Delay Time           | <b>RESISTIVE SWITCHING</b><br>$V_{GS} = 15V$<br>$V_{DD} = 500V$<br>$I_D = 12A @ 25^\circ C$<br>$R_G = 0.6\Omega$ |     | 9    |     | ns      |
| $t_r$        | Rise Time                    |                                                                                                                  |     | 5    |     |         |
| $t_{d(off)}$ | Turn-off Delay Time          |                                                                                                                  |     | 23   |     |         |
| $t_f$        | Fall Time                    |                                                                                                                  |     | 4    |     |         |
| $E_{on}$     | Turn-on Switching Energy ⑥   | <b>INDUCTIVE SWITCHING @ 25°C</b><br>$V_{DD} = 670V, V_{GS} = 15V$<br>$I_D = 12A, R_G = 5\Omega$                 |     | 334  |     | $\mu J$ |
| $E_{off}$    | Turn-off Switching Energy    |                                                                                                                  |     | 77   |     |         |
| $E_{on}$     | Turn-on Switching Energy ⑥   | <b>INDUCTIVE SWITCHING @ 125°C</b><br>$V_{DD} = 670V, V_{GS} = 15V$<br>$I_D = 12A, R_G = 5\Omega$                |     | 672  |     |         |
| $E_{off}$    | Turn-off Switching Energy    |                                                                                                                  |     | 100  |     |         |

## SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

| Symbol    | Characteristic / Test Conditions                                    | MIN                 | TYP | MAX | UNIT    |
|-----------|---------------------------------------------------------------------|---------------------|-----|-----|---------|
| $I_S$     | Continuous Source Current (Body Diode)                              |                     |     | 12  | Amps    |
| $I_{SM}$  | Pulsed Source Current ① (Body Diode)                                |                     |     | 48  |         |
| $V_{SD}$  | Diode Forward Voltage ② ( $V_{GS} = 0V, I_S = -I_D 12A$ )           |                     |     | 1.3 | Volts   |
| $dv/dt$   | Peak Diode Recovery $dv/dt$ ⑤                                       |                     |     | 18  | V/ns    |
| $t_{rr}$  | Reverse Recovery Time<br>( $I_S = -I_D 12A, di/dt = 100A/\mu s$ )   | $T_j = 25^\circ C$  |     | 200 | ns      |
|           |                                                                     | $T_j = 125^\circ C$ |     | 350 |         |
| $Q_{rr}$  | Reverse Recovery Charge<br>( $I_S = -I_D 12A, di/dt = 100A/\mu s$ ) | $T_j = 25^\circ C$  | 0.7 |     | $\mu C$ |
|           |                                                                     | $T_j = 125^\circ C$ | 2.0 |     |         |
| $I_{RRM}$ | Peak Recovery Current<br>( $I_S = -I_D 12A, di/dt = 100A/\mu s$ )   | $T_j = 25^\circ C$  | 10  |     | Amps    |
|           |                                                                     | $T_j = 125^\circ C$ | 15  |     |         |

## THERMAL CHARACTERISTICS

| Symbol          | Characteristic      | MIN | TYP | MAX  | UNIT         |
|-----------------|---------------------|-----|-----|------|--------------|
| $R_{\theta JC}$ | Junction to Case    |     |     | 0.42 | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction to Ambient |     |     | 40   |              |

① Repetitive Rating: Pulse width limited by maximum junction temperature

② Pulse Test: Pulse width < 380  $\mu s$ , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting  $T_j = +25^\circ C$ ,  $L = 16.8mH$ ,  $R_G = 25\Omega$ , Peak  $I_L = 12A$

⑤  $dv/dt$  numbers reflect the limitations of the test circuit rather than the device itself.  $I_S \leq -I_D 12A$   $di/dt \leq 700A/\mu s$   $v_R \leq V_{DSS}$   $T_j \leq 150^\circ C$

⑥  $E_{on}$  includes diode reverse recovery measured in accordance with JEDEC standard JESD24-1. See figures 18, 20.

APT Reserves the right to change, without notice, the specifications and information contained herein.

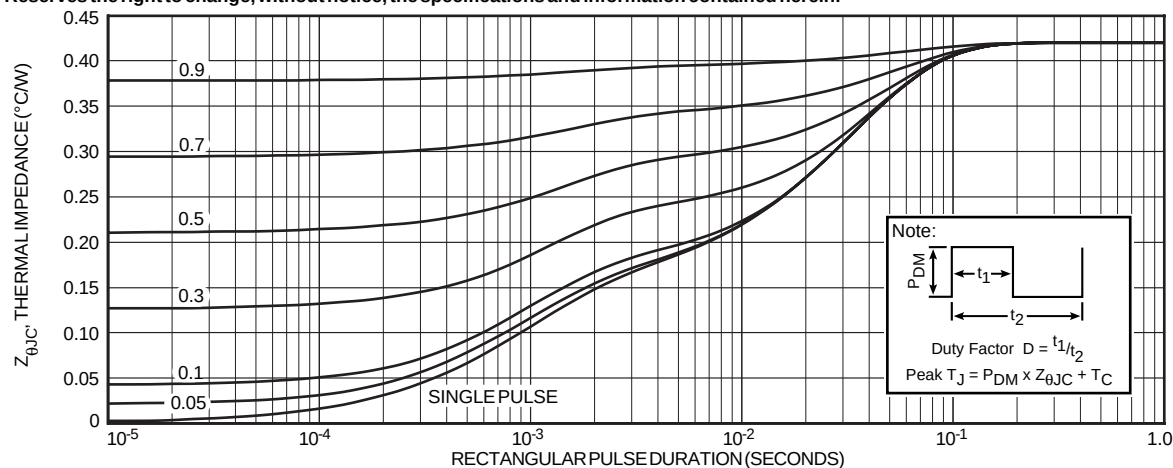


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

## Typical Performance Curves

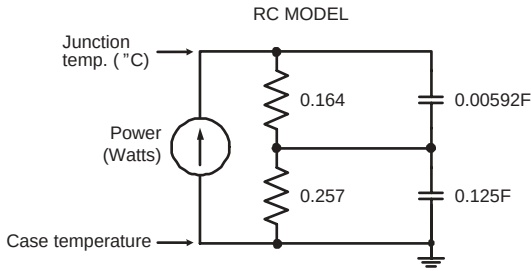


FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

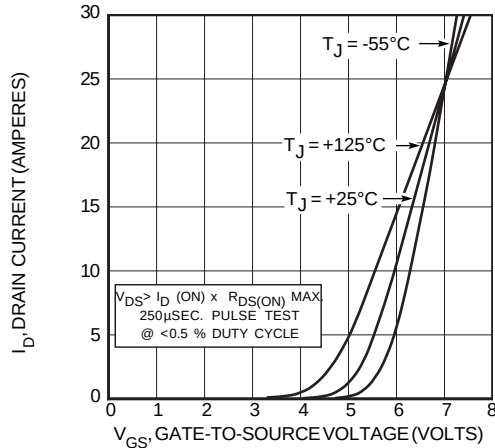


FIGURE 4, TRANSFER CHARACTERISTICS

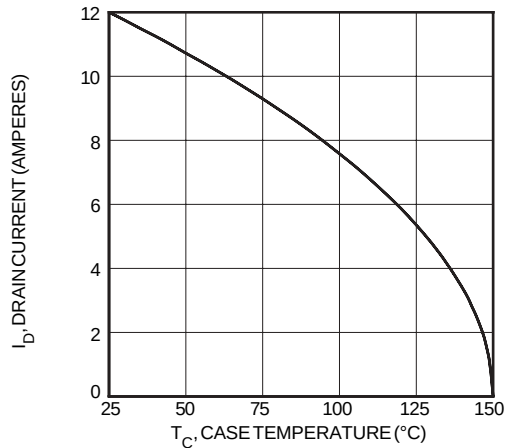


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

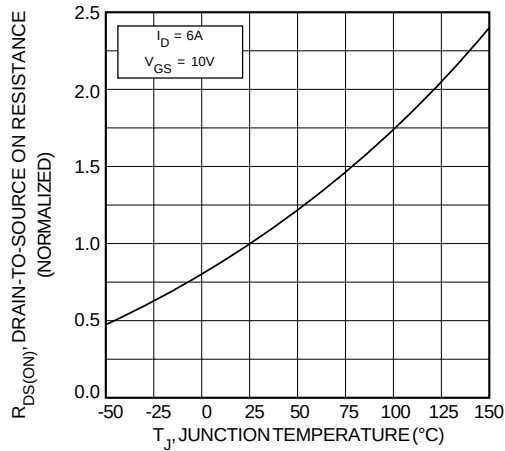


FIGURE 8,  $R_{DS(ON)}$  vs. TEMPERATURE

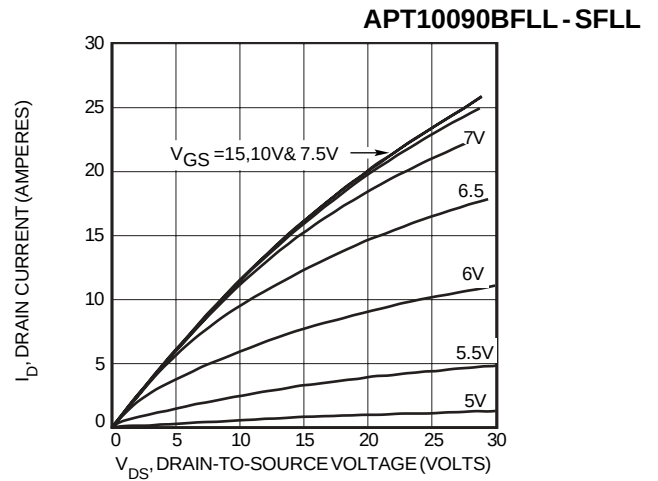


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

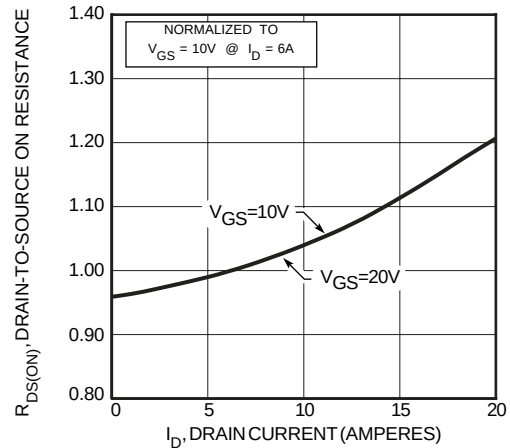


FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT

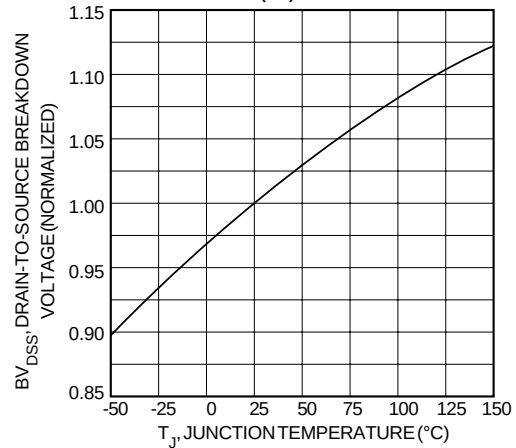


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

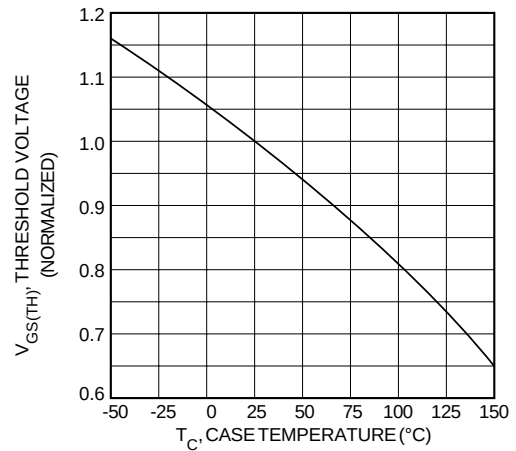


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

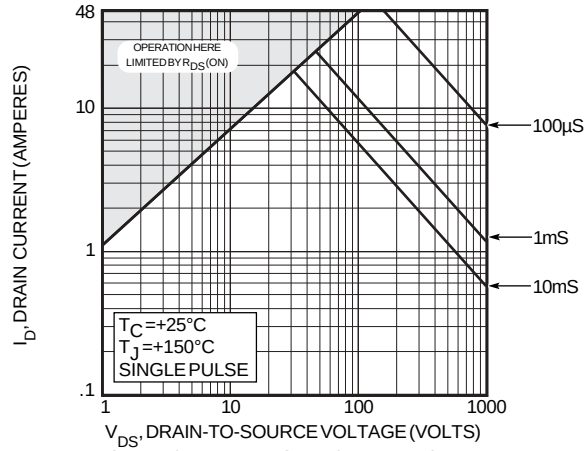


FIGURE 10, MAXIMUM SAFE OPERATING AREA

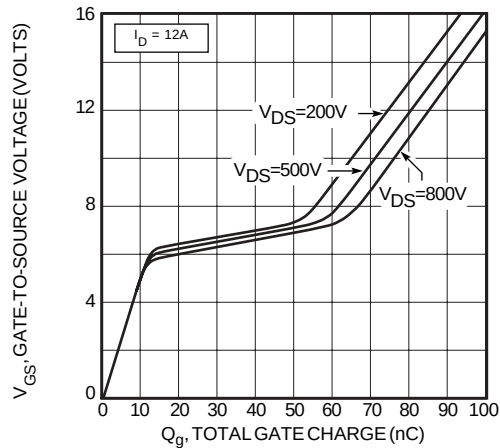


FIGURE 12, GATE CHARGE vs GATE-TO-SOURCE VOLTAGE

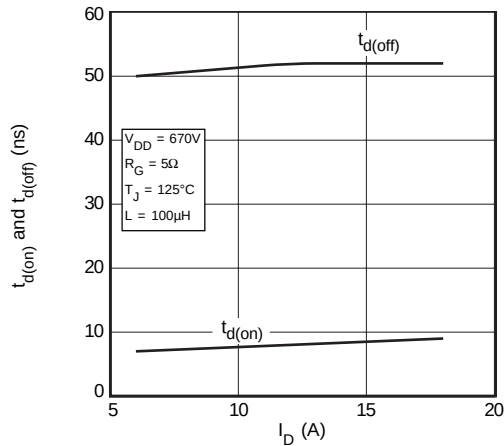


FIGURE 14, DELAY TIMES vs CURRENT

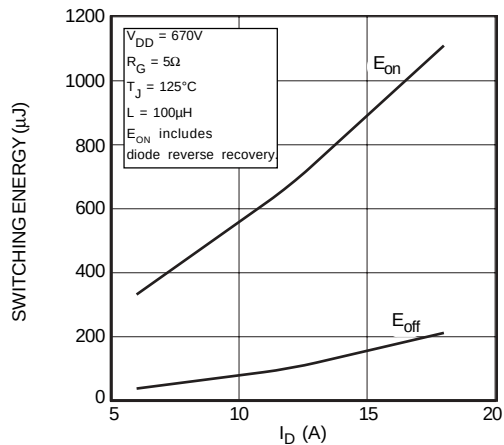


FIGURE 16, SWITCHING ENERGY vs CURRENT

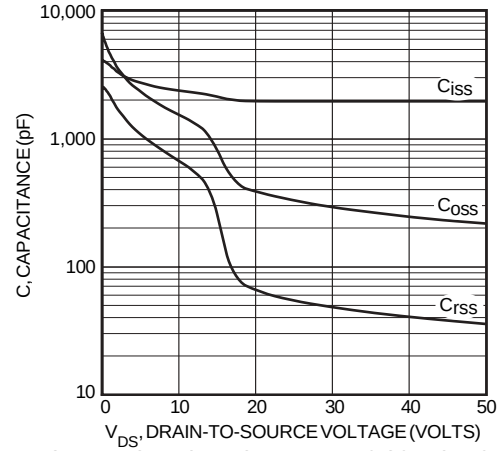


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

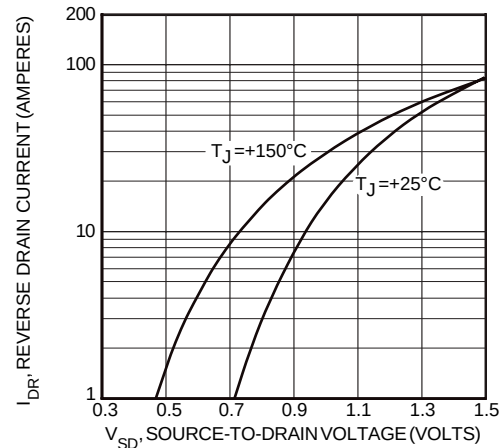


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

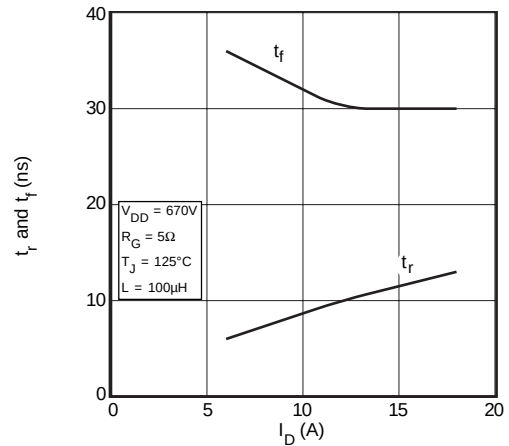


FIGURE 15, RISE AND FALL TIMES vs CURRENT

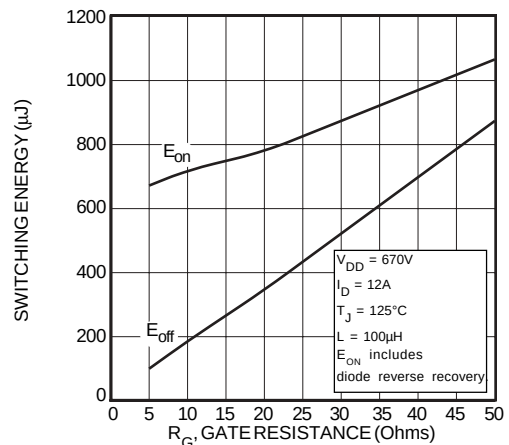
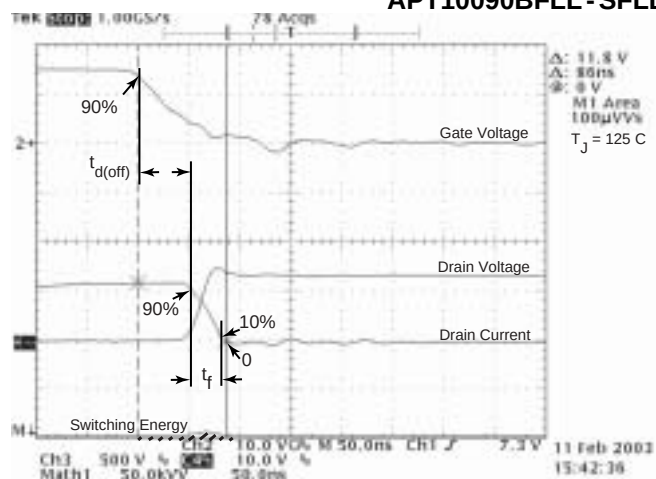
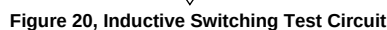


FIGURE 17, SWITCHING ENERGY vs. GATE RESISTANCE

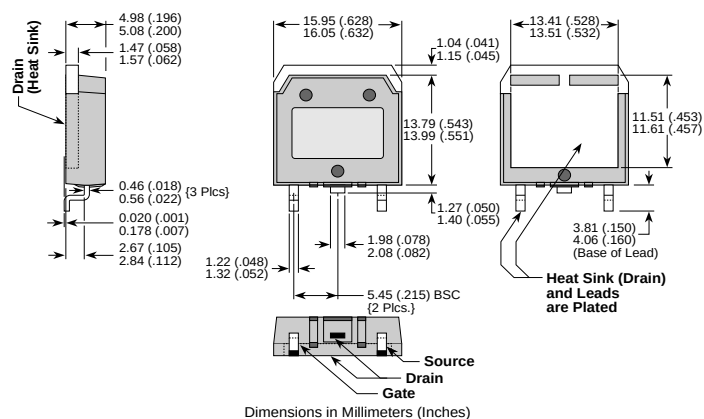
**APT10090BFLL - SFLL**



### Figure 19, Turn-off Switching Waveforms and Definitions



## D<sup>3</sup>PAK Package Outline



|           |           |           |           |           |           |
|-----------|-----------|-----------|-----------|-----------|-----------|
| 4,895,810 | 5,045,903 | 5,089,434 | 5,182,234 | 5,019,522 | 5,262,336 |
| 5,256,583 | 4,748,103 | 5,283,202 | 5,231,474 | 5,434,095 | 5,528,058 |